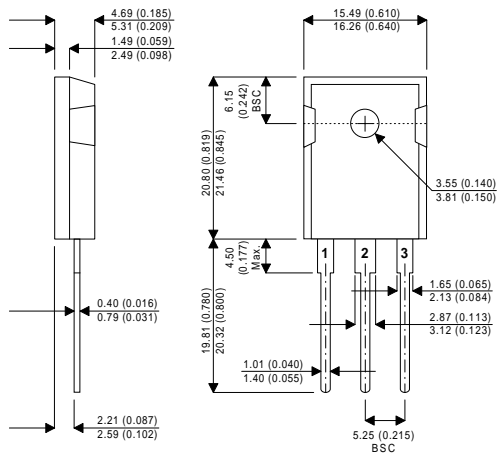


## 4TH GENERATION MOSFET

TO247-AD Package Outline.  
Dimensions in mm (inches)



**N-CHANNEL  
ENHANCEMENT MODE  
HIGH VOLTAGE  
POWER MOSFETS**

**$V_{DSS}$             800V**  
 **$I_{D(cont)}$         5.5A**  
 **$R_{DS(on)}$         2.50 $\Omega$**

**Terminal 1** Gate            **Terminal 2** Drain  
**Terminal 3** Source

### ABSOLUTE MAXIMUM RATINGS ( $T_{case} = 25^{\circ}C$ unless otherwise stated)

$V_{DSS}$	Drain – Source Voltage	800	V
$I_D$	Continuous Drain Current	5.5	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	22	A
$V_{GS}$	Gate – Source Voltage	$\pm 30$	V
$P_D$	Total Power Dissipation @ $T_{case} = 25^{\circ}C$	180	W
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to 150	$^{\circ}C$
$T_L$	Lead Temperature : 0.063" from Case for 10 Sec.	300	

### STATIC ELECTRICAL RATINGS ( $T_{case} = 25^{\circ}C$ unless otherwise stated)

	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain – Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	800			V
$I_{DSS}$	Zero Gate Voltage Drain Current ( $V_{GS} = 0V$ )	$V_{DS} = V_{DSS}$			250	$\mu A$
		$V_{DS} = 0.8V_{DSS}, T_C = 125^{\circ}C$			1000	
$I_{GSS}$	Gate – Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			$\pm 100$	nA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 1.0mA$	2		4	V
$I_{D(ON)}$	On State Drain Current <sup>2</sup>	$V_{DS} > I_{D(ON)} \times R_{DS(ON)}^{Max}$ $V_{GS} = 10V$	5.5			A
$R_{DS(ON)}$	Drain – Source On State Resistance <sup>2</sup>	$V_{GS} = 10V, I_D = 0.5 I_D [Cont.]$			2.50	$\Omega$

1) Repetitive Rating: Pulse Width limited by maximum junction temperature.

2) Pulse Test: Pulse Width < 380 $\mu S$ , Duty Cycle < 2%

**DYNAMIC CHARACTERISTICS**

	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0V$		790	950	pF
$C_{oss}$	Output Capacitance	$V_{DS} = 25V$		116	163	
$C_{rss}$	Reverse Transfer Capacitance	$f = 1MHz$		44	66	
$Q_g$	Total Gate Charge <sup>3</sup>	$V_{GS} = 10V$		38	55	nC
$Q_{gs}$	Gate – Source Charge	$V_{DD} = 0.5 V_{DSS}$		4.5	7	
$Q_{gd}$	Gate – Drain (“Miller”) Charge	$I_D = I_D [Cont.] @ 25^\circ C$		16	24	
$t_{d(on)}$	Turn-on Delay Time	$V_{GS} = 15V$		10	20	ns
$t_r$	Rise Time	$V_{DD} = 0.5 V_{DSS}$		11	21	
$t_{d(off)}$	Turn-off Delay Time	$I_D = I_D [Cont.] @ 25^\circ C$		35	53	
$t_f$	Fall Time	$R_G = 1.8\Omega$		13	26	

**SOURCE – DRAIN DIODE RATINGS AND CHARACTERISTICS**

	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current	(Body Diode)			5.5	A
$I_{SM}$	Pulsed Source Current <sup>1</sup>	(Body Diode)			22	
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS} = 0V, I_S = -I_D [Cont.]$			1.3	V
$t_{rr}$	Reverse Recovery Time	$I_S = -I_D [Cont.], di_S / dt = 100A/\mu s$	160	320	640	ns
$Q_{rr}$	Reverse Recovery Charge		1.5	3.0	6.0	$\mu C$

**SAFE OPERATING AREA CHARACTERISTICS**

	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
SOA1	Safe Operating Area	$V_{DS} = 0.4V_{DSS}, t = 1 \text{ Sec.}$ $I_{DS} = P_D / 0.4V_{DSS}$	180			W
SOA2	Safe Operating Area	$V_{DS} = P_D / I_D [Cont.]$ $I_{DS} = I_D [Cont.], t = 1 \text{ Sec.}$	180			W
$I_{LM}$	Inductive Current Clamped		22			A

**THERMAL CHARACTERISTICS**

	Characteristic	Min.	Typ.	Max.	Unit
$R_{\theta JC}$	Junction to Case			0.68	$^\circ C/W$
$R_{\theta JA}$	Junction to Ambient			40	

1) Repetitive Rating: Pulse Width limited by maximum junction temperature.

2) Pulse Test: Pulse Width < 380 $\mu s$ , Duty Cycle < 2%

3) See MIL–STD–750 Method 3471



CAUTION — Electrostatic Sensitive Devices. Anti-Static Procedures Must Be Followed.